

Data Sheet Issue: - 2

Soft Recovery Diode Type M0859LC140 to M0859LC180

(Old Type No.: SM02-16CXC220)

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V _{RRM}	Repetitive peak reverse voltage, (note 1)	1400-1800	V
Vrsm	Non-repetitive peak reverse voltage, (note 1)	1500-1900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{F(AV)M}	Maximum average forward current, T _{sink} =55°C, (note 2)	859	А
IF(AV)M	Maximum average forward current. T _{sink} =85°C, (note 2)	562	А
IF(AV)M	Maximum average forward. T _{sink} =85°C, (note 3)	319	А
F(RMS)	Nominal RMS forward current, T _{sink} =25°C, (note 2)	1742	А
I _{f(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 4)	1404	А
IFSM	Peak non-repetitive surge t _p =10ms, V _{RM} =60%V _{RRM} , (note 5)	10	kA
IFSM2	Peak non-repetitive surge t _p =10ms, V _{RM} ≤10V, (note 5)	11	kA
l²t	$I^{2}t$ capacity for fusing t _p =10ms, V _{RM} =60%V _{RRM} , (note 5)	500×10 ³	A ² s
l²t	$I^{2}t$ capacity for fusing t _p =10ms, V _{RM} ≤10V, (note 5)	605×10 ³	A ² s
T _{j op}	Operating temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-40 to +150	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Single side cooled, single phase; 50Hz, 180° half-sinewave.

4) Double side cooled.

5) Half-sinewave, 125°C T_j initial.



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS	
Vfm	Maximum pack forward voltage	-	-	1.55	I _{FM} =1200A	V	
VFM	Maximum peak forward voltage	-	-	1.7	I _{FM} =1750A		
V _{T0}	Threshold voltage	-	-	1.17		V	
r T	Slope resistance	-	-	0.32		mΩ	
Vfrm	Maximum forward recovery voltage	-	-	20	di/dt = 1000A/µs, Tj=25°C	V	
		-	-	30	di/dt = 1000A/µs	V	
I _{RRM}	Peak reverse current	-	-	50	Rated V _{RRM}	mA	
Qrr	Recovered charge	-	280	-		μC	
Q _{ra}	Recovered charge, 50% Chord	-	110	140	I _{FM} =800A, t _P =500μs, di/dt=50A/μs, V _r =50V,	μC	
Irm	Reverse recovery current	-	75	-	50% Chord.	А	
trr	Reverse recovery time, 50% Chord	-	3	-		μs	
R _{thJK}	Thermal resistance, junction to heatsink	-	-	0.044	Double side cooled		
		-	-	0.088	Single side cooled	K/W	
F	Mounting force	10	-	20		kN	
Wt	Weight	-	340	-		g	

Notes:-

1) Unless otherwise indicated $T_j=125^{\circ}C$.



Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} (V)	V _{RSM} (V)	V _R dc (V)
14	1400	1500	930
16	1600	1700	1040
18	1800	1900	1200

2.0 De-rating Factor

A blocking voltage de-rating factor of 0.13% per °C is applicable to this device for T_i below 25°C.

3.0 ABCD Constants

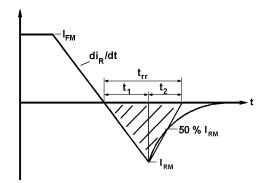
These constants (applicable only over current range of VF characteristic in Figure 1) are the coefficients of the expression for the forward characteristic given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

where I_F = instantaneous forward current.

4.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig.(a) below.



(ii) Q_{rr} is based on a 150µs integration time.

$$Q_{rr} = \int_{0}^{150\,\mu s} i_{rr}.dt$$

I.e.

(iii)
$$K \ Factor = \frac{t_1}{t_2}$$

4



5.0 Reverse Recovery Loss

The following procedure is recommended for use where it is necessary to include reverse recovery loss.

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be E joules per pulse. A new sink temperature can then be evaluated from:

$$T_{SINK} = T_{j(MAX)} - E \cdot \left[k + f \cdot R_{thJK}\right]$$

Where k = 0.2314 (°C/W)/s

- E = Area under reverse loss waveform per pulse in joules (W.s.)
- f = Rated frequency in Hz at the original sink temperature.
- $R_{th(JK)} = d.c.$ thermal resistance (°C/W)

The total dissipation is now given by:

$$W_{\scriptscriptstyle (tot)} = W_{\scriptscriptstyle (original)} + E \cdot f$$

NOTE 1 - Reverse Recovery Loss by Measurement

This device has a low reverse recovered charge and peak reverse recovery current. When measuring the charge, care must be taken to ensure that:

(a) AC coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.

(b) A suitable, polarised, clipping circuit must be connected to the input of the measuring oscilloscope to avoid overloading the internal amplifiers by the relatively high amplitude forward current signal.

(c) Measurement of reverse recovery waveform should be carried out with an appropriate critically damped snubber, connected across diode anode to cathode. The formula used for the calculation of this snubber is shown below:

$$R^2 = 4 \cdot \frac{V_r}{C_s \cdot \frac{di}{dt}}$$

Where: Vr = Commutating source voltage

Cs = Snubber capacitance

R = Snubber resistance

6.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.



7.0 Computer Modelling Parameters

7.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_o + \sqrt{V_o + 4 \cdot ff^2 \cdot r_s \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_s}$$

Where $V_{T0} = 1.17$ V, $r_T = 0.32$ m Ω

ff = form factor (normally unity for fast diode applications)

$$W_{AV} = \frac{\Delta T}{R_{th}}$$
$$\Delta T = T_{i(MAX)} - T_{k}$$

7.2 Calculation of VF using ABCD Coefficients

The forward characteristic IF Vs VF, on page 6 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, and D forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given in this report for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients		
Α	0.9692108214	А	0.5014768256	
В	0.0334639000	В	0.1050145000	
С	8.17008×10⁻⁵	С	1.371460×10 ⁻⁴	
D	9.5403280×10 ⁻³	D	4.0237590×10 ⁻³	

8.0 Frequency Ratings

The curves illustrated in figures 8 to 16 are for guidance only and are superseded by the maximum ratings shown on page 1.

9.0 Square wave ratings

These ratings are given for load component rate of rise of forward current of 100 and 500 A/µs.

10.0 Duty cycle lines

The 100% duty cycle is represented on all the ratings by a straight line. Other duties can be included as parallel to the first.



Curves

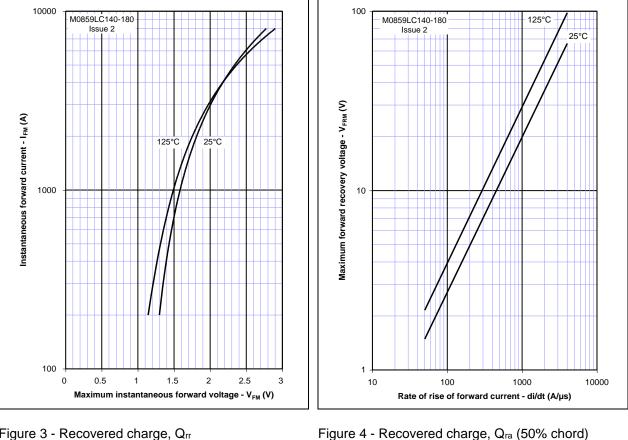


Figure 1 - Forward characteristics of Limit device

Figure 2 - Maximum forward recovery voltage



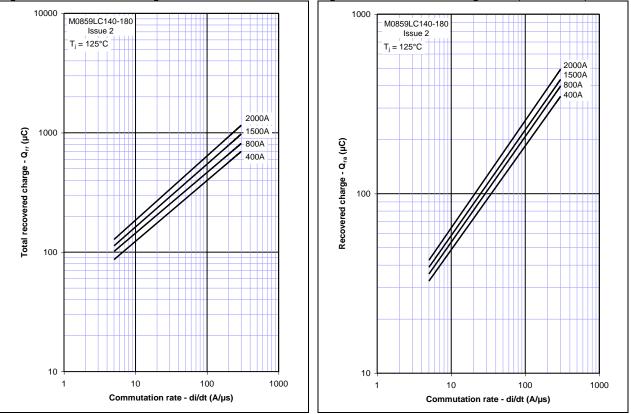




Figure 5 - Maximum reverse current, Irm

1000 M0859LC140-180 Issue 2 T_i = 125°C 2000A 1500A 800A 400A Reverse recovery current - I_{rm} (A) 100 10 1 10 100 1000 Commutation rate - di/dt (A/µs)



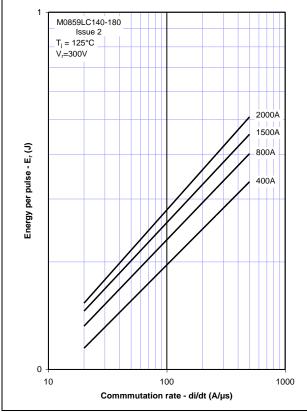


Figure 6 - Maximum recovery time, trr (50% chord)

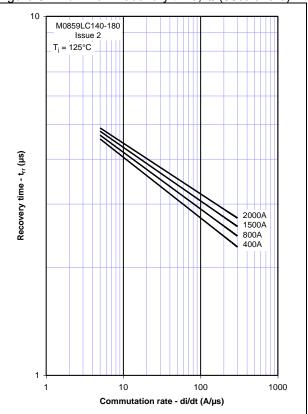
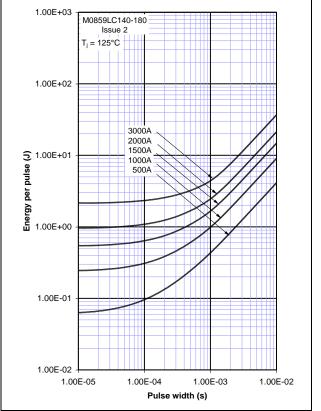
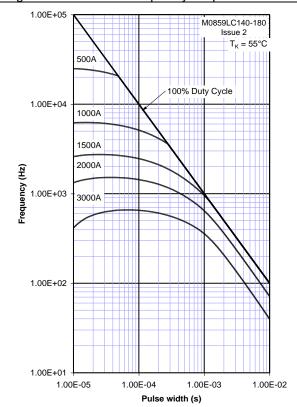
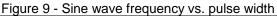


Figure 8 - Sine wave energy per pulse

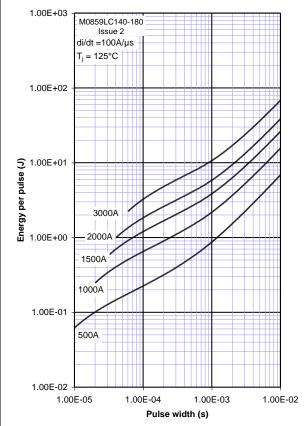


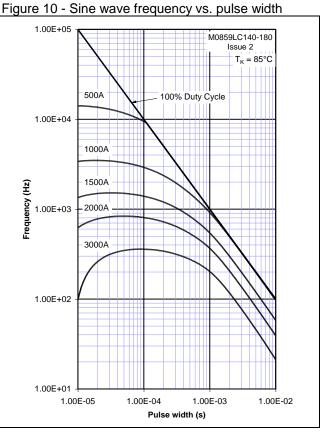


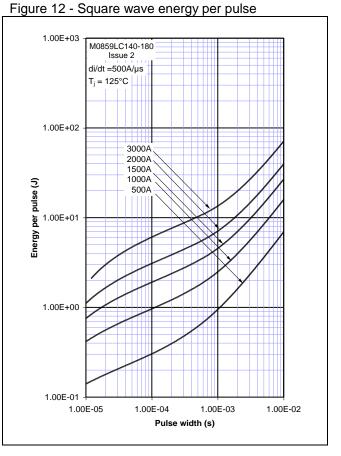














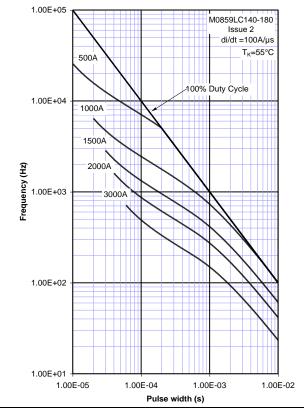
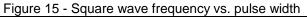
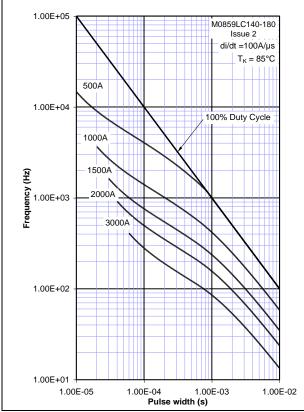


Figure 13 - Square wave frequency vs. pulse width







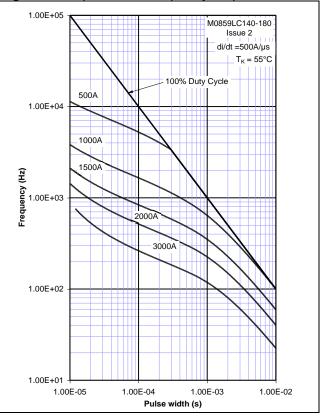


Figure 16 - Square wave frequency vs. pulse width

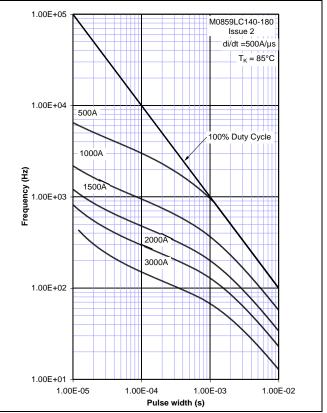
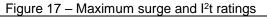


Figure 14 - Square wave frequency vs. pulse width





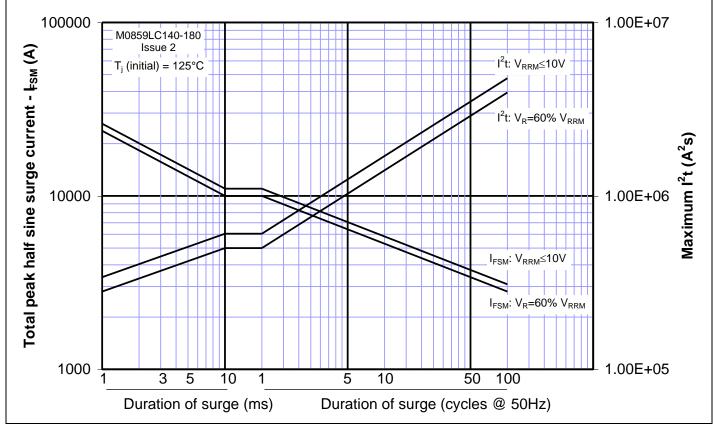
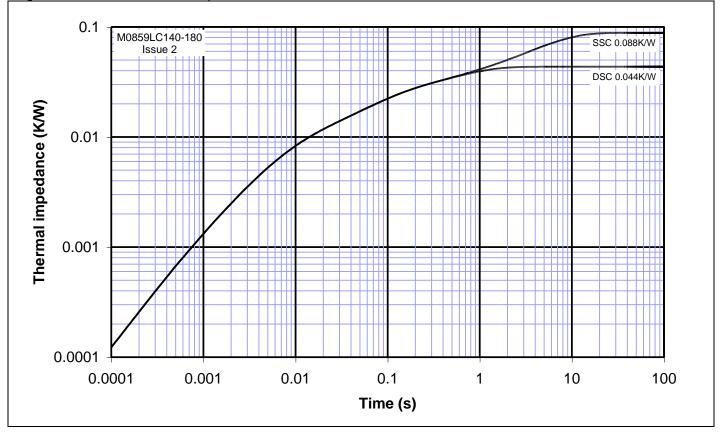
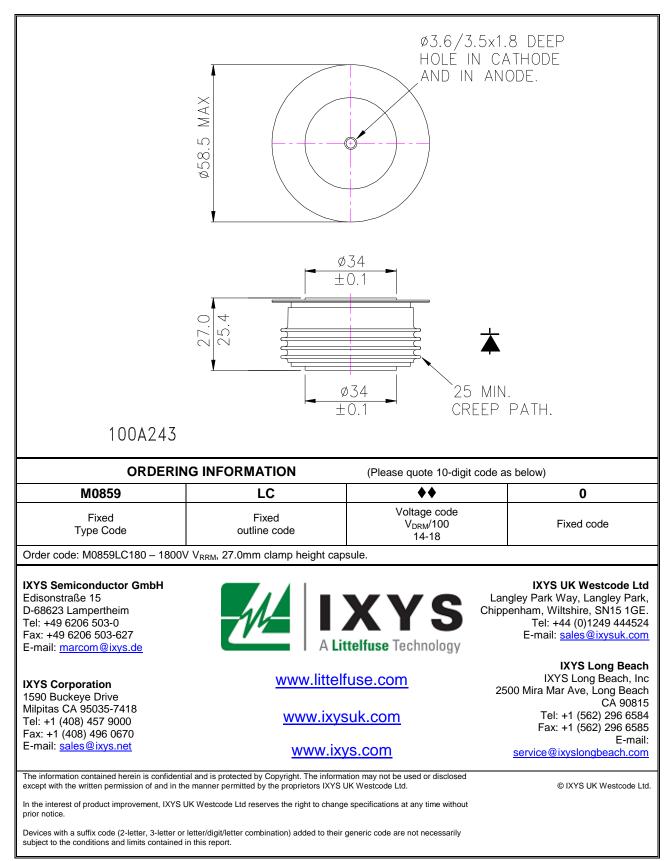


Figure 18 – Transient thermal impedance





Outline Drawing & Ordering Information





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